



MMDT2227

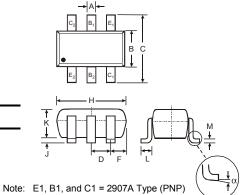
COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Complementary Pairs** One 2222A Type (NPN) One 2907A Type (PNP)
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

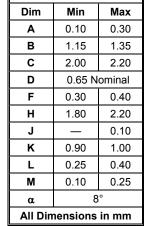
Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe)
- Terminal Connections: See Diagram
- Ordering & Date Code Information: See Page 4
- Marking Information: K27, See Page 4
- Weight: 0.006 grams (approximate)



E2, B2, and C2 = 2222A Type (NPN)

Type marking indicates orientation



SOT-363

Maximum Ratings, Total Device @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit		
Total Power Dissipation	(Note 1)	Pd	200	mW		
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ ext{ heta}JA}$	625	°C/W		
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C		

Maximum Ratings, 2222A Type (NPN) @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous	Ι _C	600	mA

Maximum Ratings, 2907A Type (PNP) @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous	Ι _C	-600	mA

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout

document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

No purposefully added lead. 2.

3.

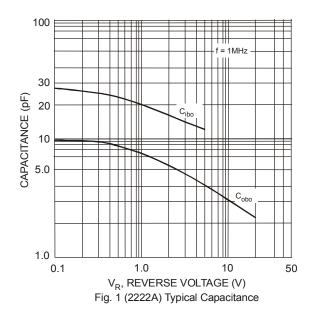
Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date 4 Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

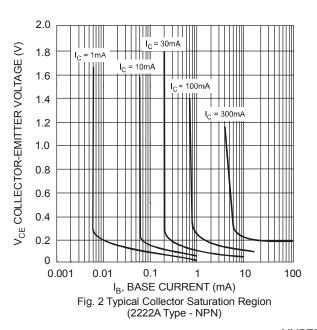


Electrical Characteristics, 2222A Type (NPN) @T_A = 25°C unless otherwise specified

Liectrical Characteristics, 2222A Type (IFR) @T _A = 25 C unless otherwise specified										
Characteristic	Symbol	Min	Max	Unit	Test Condition					
OFF CHARACTERISTICS (Note 5)			-							
Collector-Base Breakdown Voltage	V _{(BR)CBO}	75		V	$I_{C} = 10\mu A, I_{E} = 0$					
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	—	V	I _C = 10mA, I _B = 0					
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0		V	$I_{\rm E}$ = 10 μ A, $I_{\rm C}$ = 0					
Collector Cutoff Current	I _{CBO}		10	nA μA	V _{CB} = 60V, I _E = 0 V _{CB} = 60V, I _E = 0, T _A = 150°C					
Collector Cutoff Current	ICEX	_	10	nA	V _{CE} = 60V, V _{EB(OFF)} = 3.0V					
Emitter Cutoff Current	I _{EBO}	_	10	nA	V _{EB} = 3.0V, I _C = 0					
Base Cutoff Current	I _{BL}	_	20	nA	$V_{CE} = 60V, V_{EB(OFF)} = 3.0V$					
ON CHARACTERISTICS (Note 5)										
DC Current Gain	h _{FE}	35 50 75 100 40 50 35	 300 		$\begin{split} I_{C} &= 100 \mu A, V_{CE} = 10V \\ I_{C} &= 1.0 mA, V_{CE} = 10V \\ I_{C} &= 10 mA, V_{CE} = 10V \\ I_{C} &= 150 mA, V_{CE} = 10V \\ I_{C} &= 500 mA, V_{CE} = 10V \\ I_{C} &= 10 mA, V_{CE} = 10V, T_{A} = -55^{\circ}C \\ I_{C} &= 150 mA, V_{CE} = 1.0V \end{split}$					
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.3 1.0	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA					
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.6	1.2 2.0	V	I_{C} = 150mA, I_{B} = 15mA I_{C} = 500mA, I_{B} = 50mA					
SMALL SIGNAL CHARACTERISTICS				•	•					
Output Capacitance	C _{obo}	_	8	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0					
Input Capacitance	Cibo	_	25	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0					
Current Gain-Bandwidth Product	f _T	300	_	MHz	V _{CE} = 20V, I _C = 20mA, f = 100MHz					
Noise Figure	NF		4.0	dB	V _{CE} = 10V, I _C = 100μA, R _S = 1.0kΩ, f = 1.0kHz					
SWITCHING CHARACTERISTICS	•				·					
Delay Time	t _d	_	10	ns	V _{CC} = 30V, I _C = 150mA,					
Rise Time	tr		25	ns	$V_{BE(off)} = -0.5V, I_{B1} = 15mA$					
Storage Time	ts	_	225	ns	V _{CC} = 30V, I _C = 150mA,					
Fall Time	t _f		60	ns	$I_{B1} = I_{B2} = 15 \text{mA}$					
	1			(

Note: 5. Pulse test: Pulse width \leq 300µs, duty cycle \leq 2%.







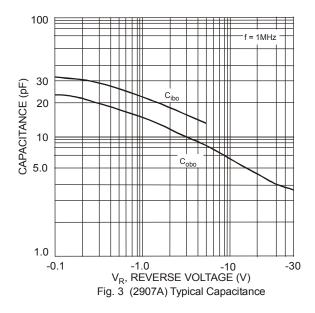
Electrical Characteristics, 2907A Type (PNP) @T_A = 25°C unless otherwise specified

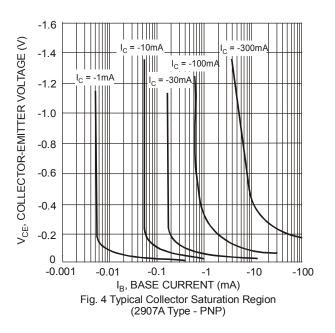
Characteristic	Symbol	Min	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 6)								
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-60		V	$I_{\rm C} = -10 \mu {\rm A}, \ I_{\rm E} = 0$			
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60		V	I _C = -10mA, I _B = 0			
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		V	$I_{\rm E} = -10 \mu A, I_{\rm C} = 0$			
Collector Cutoff Current	I _{CBO}	_	-10	nA μA	V _{CB} = -50V, I _E = 0 V _{CB} = -50V, I _E = 0, T _A = 125°C			
Collector Cutoff Current	I _{CEX}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$			
Base Cutoff Current	I _{BL}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$			
ON CHARACTERISTICS (Note 6)	•				•			
DC Current Gain	h _{FE}	75 100 100 100 50	 300	_	$\begin{split} I_{C} &= -100 \mu A, \ V_{CE} &= -10V \\ I_{C} &= -1.0 m A, \ V_{CE} &= -10V \\ I_{C} &= -10 m A, \ V_{CE} &= -10V \\ I_{C} &= -150 m A, \ V_{CE} &= -10V \\ I_{C} &= -500 m A, \ V_{CE} &= -10V \end{split}$			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.4 -1.6	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA			
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-1.3 -2.6	V	I_{C} = 150mA, I_{B} = 15mA I_{C} = 500mA, I_{B} = 50mA			
SMALL SIGNAL CHARACTERISTICS		-	-	-				
Output Capacitance	C _{obo}	—	8.0	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0			
Input Capacitance	Cibo	—	30	pF	V_{EB} = -2.0V, f = 1.0MHz, I _C = 0			
Current Gain-Bandwidth Product	f⊤	200	_	MHz	V _{CE} = -20V, I _C = -50mA, f = 100MHz			
SWITCHING CHARACTERISTICS								
Turn-On Time	t _{on}	—	45	ns	—			
Delay Time	t _d	—	10	ns	V _{CC} = -30V, I _C = -150mA,			
Rise Time	tr	—	40	ns	I _{B1} = -15mA			
Turn-Off Time	t _{off}		100	ns	—			
Storage Time	ts	—	80	ns	V _{CC} = -6.0V, I _C = -150mA,			
Fall Time	t _f		30	ns	$I_{B1} = I_{B2} = -15 \text{mA}$			

Notes:

6.

Short duration pulse test used to minimize self-heating effect.





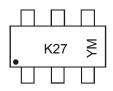


Ordering Information (Note 7)

Device	Packaging	Shipping			
MMDT2227-7-F	SOT-363	3000/Tape & Reel			

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K27 = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	К	L	М	N	Р	R	S	Т	U	V	W	Х	Y	Z
Month	Jan	Fel	b I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t I	Vov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D

IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.